

IN THE CLAIMS

Please amend the claims presently in the application as follows:

ad 4. (Amended) The polishing medium for chemical-mechanical polishing according to claim 1, which has a coefficient of kinetic friction of 0.25 or more.

5. (Amended) The polishing medium for chemical-mechanical polishing according to claim 1, which has a Ubbelode's viscosity of 0.95 mPa's (0.95 cP) or more and 1.5 mPa's (1.5 cP) or less.

6. (Amended) The polishing medium for chemical-mechanical polishing according to claim 1, which has a point-of-inflection pressure of 5 kPa (50 gf/cm²) or more.

7. (Amended) The polishing medium for chemical-mechanical polishing according to claim 1, wherein said oxidizing agent is at least one of hydrogen peroxide, nitric acid, potassium periodate, hypochlorous acid and ozone water.

8. (Amended) The polishing medium for chemical-mechanical

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polishing according to claim 1, wherein said metal-oxide-dissolving agent is at least one of an organic acid, an organic-acid ester, an organic-acid ammonium salt and sulfuric acid.

9. (Amended) The polishing medium for chemical-mechanical polishing according to claim 1, wherein said protective-film-forming agent is a nitrogen-containing compound.

10. (Amended) The polishing medium for chemical-mechanical polishing according to claim 1, wherein said protective-film-forming agent is at least one of a mercaptan, glucose and cellulose.

11. (Amended) A polishing method comprising polishing a polishing object film of a metal or metal oxide with the polishing medium for chemical-mechanical polishing according to claim 1.

IN THE ABSTRACT

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Please amend the abstract as follows:

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This invention provides a polishing medium for CMP, comprising an oxidizing agent, a metal-oxide-dissolving agent, a protective-film-forming agent,